DISCRETE SEMICONDUCTORS

DATA SHEET

PEMB11; PUMB11 PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

Product specification Supersedes data of 2001 Sep 13 2003 Oct 03





kΩ

 $k\Omega$

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

PEMB11; PUMB11

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
TR1	PNP	_	_	_
TR2	PNP	_	_	_

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QUICK REFERENCE DATA

bias resistor

bias resistor

DESCRIPTION

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	(AGE	MARKING CODE(1)	NPN/PNP	NPN/NPN
I TPE NOWIBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMB11	SOT666	_	B1	PEMD3	PEMH11
PUMB11	SOT363	SC-88	B*1	PUMD3	PUMH11

R1

R2

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING
I TPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION
PEMB11	6 5 4	1	emitter TR1
PUMB11	6 5 4	2	base TR1
	R1 R2	3	collector TR2
	TR2	4	emitter TR2
	TR1	5	base TR2
	$\left[\begin{array}{c c} & R2 \\ \hline \end{array}\right]$ R2 $\left[\begin{array}{c c} R1 \end{array}\right]$	6	collector TR1
	1 2 3		
	1 2 3 Top view MAM477		
	man#//		

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PEMB11; PUMB11

ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
I TPE NOWIBER	NAME	DESCRIPTION	VERSION
PEMB11	_	plastic surface mounted package; 6 leads	SOT666
PUMB11	_	plastic surface mounted package; 6 leads	SOT363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT						
Per transis	Per transistor										
V _{CBO}	collector-base voltage	open emitter	_	-50	V						
V _{CEO}	collector-emitter voltage	open base	_	-50	V						
V _{EBO}	emitter-base voltage	open collector	_	-10	V						
VI	input voltage										
	positive		_	+10	V						
	negative		_	-40	V						
Io	output current (DC)		_	-100	mA						
I _{CM}	peak collector current	eak collector current –									
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C									
	SOT363	note 1	-	200	mW						
	SOT666	notes 1 and 2	_	200	mW						
T _{stg}	storage temperature		-65	+150	°C						
Tj	junction temperature		_	150	°C						
T _{amb}	operating ambient temperature		-65	+150	°C						
Per device	•										
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C									
	SOT363	note 1	_	300	mW						
	SOT666	notes 1 and 2	_	300	mW						

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0$	_	_	-400	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	30	_	_	
V _{CEsat}	saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-1.1	-0.8	V
$V_{i(on)}$	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -10 \text{ mA}$	-2.5	-1.8	_	V
R1	input resistor		7	10	13	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

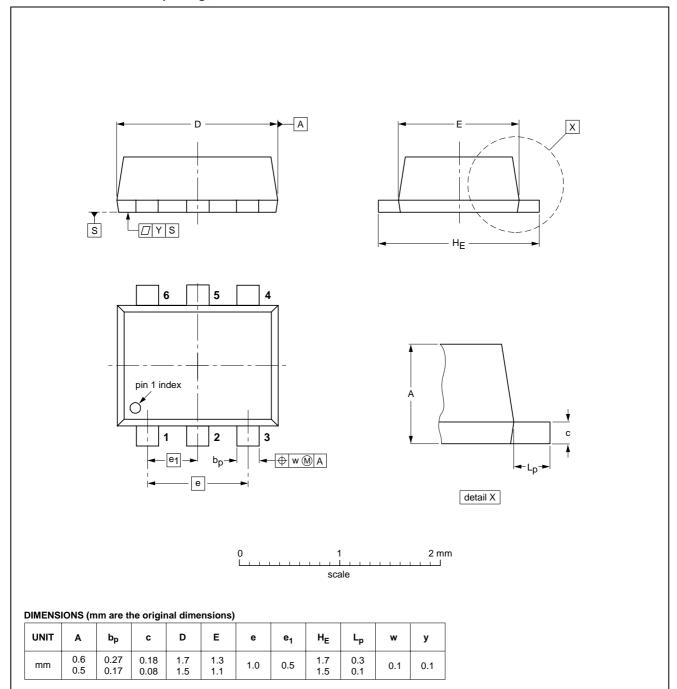
PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



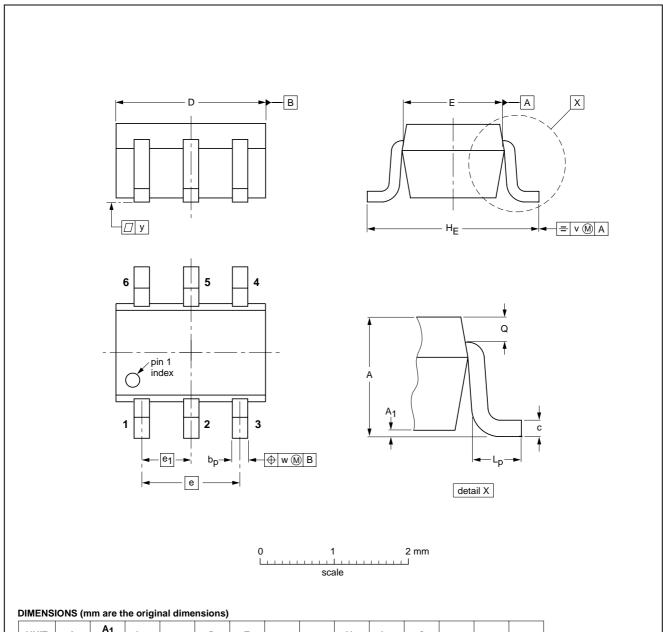
OUTLINE		REFER	FERENCES EUROPEAN ISSUE F				
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT666						-01-01-04- 01-08-27	
				1			

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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Plastic surface mounted package; 6 leads

SOT363



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	٧	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
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